

Dual N-Channel Silicon Junction Field-Effect Transistor

- Low-Noise Audio Amplifier
- Equivalent to Japanese 2SK146

Absolute maximum ratings at $T_A = 25^\circ\text{C}$

Reverse Gate Source & Reverse Gate Drain Voltage	- 40 V
Continuous Forward Gate Current	10 mA
Continuous Device Power Dissipation	375 mW
Power Derating	3 mW/ $^\circ\text{C}$
Storage Temperature Range	- 65 $^\circ\text{C}$ to 200 $^\circ\text{C}$

At 25°C free air temperature:

Static Electrical Characteristics

		IFN146			Process NJ450	
		Min	Typ	Max	Unit	Test Conditions
Gate Source Breakdown Voltage	$V_{(\text{BR})\text{GSS}}$	- 40			V	$I_G = - 1 \mu\text{A}, V_{DS} = 0\text{V}$
Gate Reverse Current	I_{GSS}			- 1	nA	$V_{GS} = - 30\text{V}, V_{DS} = 0\text{V}$
				- 1	μA	$V_{GS} = - 30\text{V}, V_{DS} = 0\text{V}$
Gate Source Cutoff Voltage	$V_{GS(\text{OFF})}$	- 0.3		- 1.2	V	$V_{DS} = 10\text{V}, I_D = 1 \mu\text{A}$
Drain Saturation Current (Pulsed)	I_{DSS}			30	mA	$V_{DS} = 10\text{V}, V_{GS} = 0\text{V}$

Dynamic Electrical Characteristics

Common Source Forward Transconductance	g_{fs}	30	40		mS	$V_{DS} = 10\text{V}, V_{GS} = 0\text{V}$ $I_{DSS} = 5 \text{ mA}$	f = 1 kHz
Common Source Input Capacitance	C_{iss}			75	pF	$V_{DS} = 10\text{V}, V_{GS} = 0\text{V}$	f = 1 kHz
Common Source Reverse Transfer Capacitance	C_{rss}			15	pF	$V_{DS} = 10\text{V}, I_D = 0\text{A}$	f = 1 kHz
Noise Figure	NF		1		dB	$V_{DS} = 10\text{V}, I_D = 5 \text{ mA}$ $R_G = 100\Omega$	f = 1 kHz
Differential Gate Source Voltage	$ V_{GS1} - V_{GS2} $			20	mV	$V_{DS} = 10\text{V}, I_D = 5 \text{ mA}$	

TO-71 Package

Dimensions in Inches (mm)

Pin Configuration

1 Source, 2 Gate, 3 Drain,
5 Source, 6 Gate, 7 Drain

